



1752/\$

PATENT
30205/37456

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Geun Su Lee et al.)
Serial No.: 09/884,313)
Filed: June 19, 2001)
For: Photoresist Polymer for Top-)
Surface Imaging Process by Silylation)
and Photoresist Composition)
Containing the Same)
Group Art Unit: 1752)
Examiner: Yvette C. Thornton)

I hereby certify that this paper and the documents referred to as enclosed therewith are being deposited with the United States Postal Service as first class mail, postage prepaid, on February 19, 2003, in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231.

Michael R. Hull
Reg. No. 35,902
Attorney for Applicants

9/2
r

RECEIVED
MAR 03 2003
GROUP 1700

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the office action mailed on November 20, 2002, please amend the above-identified patent application as follows:

In the Specification:

Please replace the paragraph beginning on page 8, line 14, with the following rewritten paragraph:

--Yet another aspect is to provide a process for forming a photoresist pattern, as shown in Fig. 1, comprising the steps of:

- (a) coating a photoresist composition on a substrate of a semiconductor element to form a photoresist film;
- (b) selectively exposing said photoresist film using a light source (see the first drawing in Fig. 1);
- (c) applying silylating agent to the resultant to produce a silylated layer on the exposed portion of said exposed photoresist film (see the second drawing in Fig. 1); and
- (d) etching the non-exposed portion photoresist film using the silylated layer as an etching mask (see the third and fourth drawings in Fig. 1).--

21